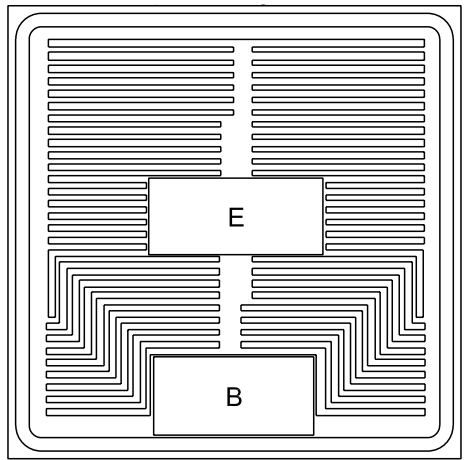


Power Transistors
8.0 Amp NPN - High Voltage Transistor Chip

PROCESS DETAILS

Die Size	167 x 167 MILS
Die Thickness	9.5 MILS
Base Bonding Pad Area	59 x 29 MILS
Emitter Bonding Pad Area	64 x 28 MILS
Top Side Metalization	Al - 45,000Å
Back Side Metalization	Ti/Ni/Ag - 3,000Å, 10,000Å, 10,000Å

GEOMETRY



BACKSIDE COLLECTOR

R0

GROSS DIE PER 5 INCH WAFER

558

PRINCIPAL DEVICE TYPES

MJE13009